

SANYO	No.2516	2SB1295/2SD1935
		PNP/NPN Epitaxial Planar Silicon Transistors Low-Frequency General-Purpose Amp Applications

Applications

- . AF power amp, medium-speed switching, small-sized motor drivers

Features

- . Large current capacity
- . Low collector to emitter saturation voltage
- . Very small-sized package permitting sets to be made smaller and slimer

(): 2SB1295

Absolute Maximum Ratings at Ta=25°C

			unit
Collector to Base Voltage	V _{CB0}	(-)15	V
Collector to Emitter Voltage	V _{CE0}	(-)15	V
Emitter to Base Voltage	V _{EB0}	(-)5	V
Collector Current	I _C	(-)0.8	A
Collector Current(Pulse)	I _{CP}	(-)3	A
Collector Dissipation	P _C	200	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Electrical Characteristics at Ta=25°C

			min	typ	max	unit
Collector Cutoff Current	I _{CB0}	V _{CB} =(-)12V, I _E =0			(-)100	nA
Emitter Cutoff Current	I _{EB0}	V _{EB} =(-)4V, I _C =0			(-)100	nA
DC Current Gain	h _{FE} (1)	V _{CE} =(-)2V, I _C =(-)50mA	135*		900* (600)	
Gain-Bandwidth Product	f _T	V _{CE} =(-)2V, I _C =(-)800mA V _{CE} =(-)2V, I _C =(-)50mA	80		200 (300)	MHz
Output Capacitance	c _{ob}	V _{CB} =(-)10V, f=1MHz		(15)10		pF

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*: The 2SB1295/2SD1935 are classified by 50mA h_{FE} as follows:

2SB1295	135	5	270	200	6	400	300	7	600
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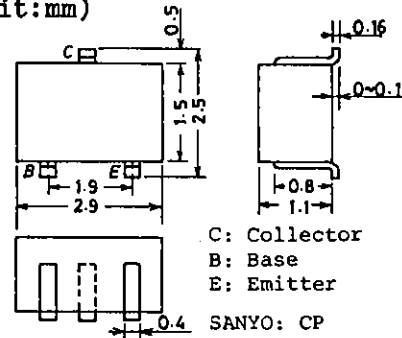
2SD1935	135	5	270	200	6	400	300	7	600	450	8	900
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Marking : 2SB1295:UL/2SD1935:CT

h_{FE} rank: 2SB1295:5,6,7/2SD1935:5,6,7,8

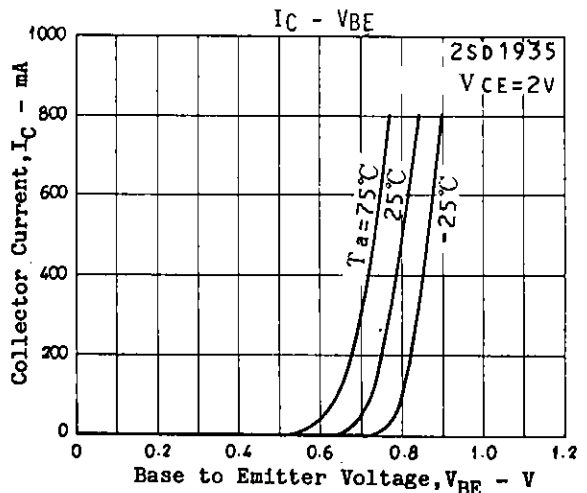
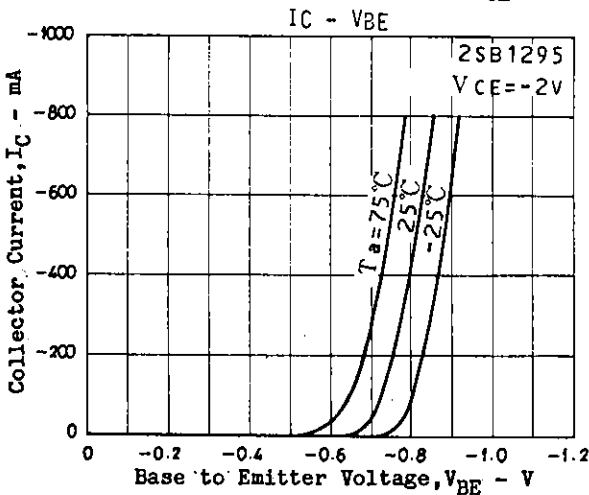
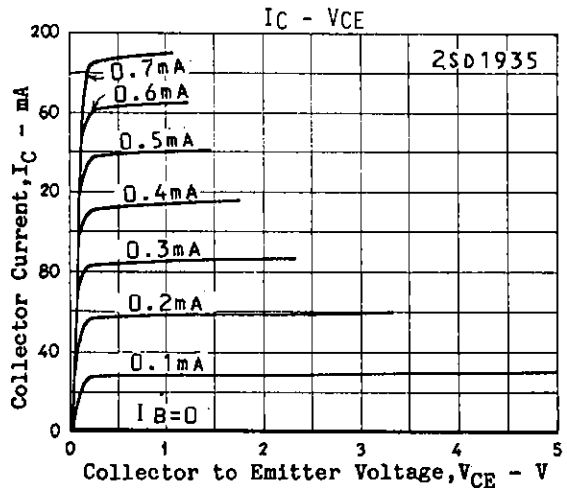
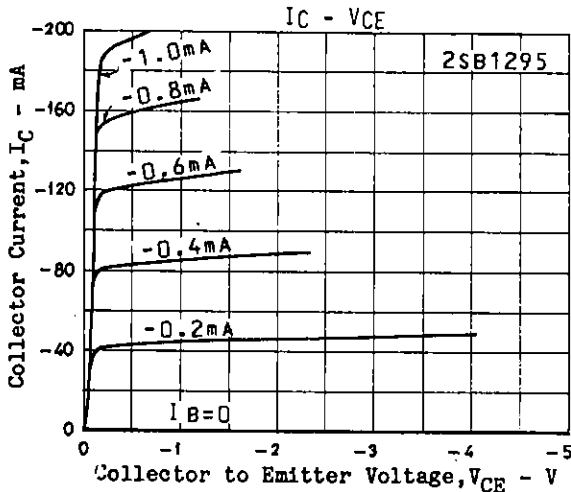
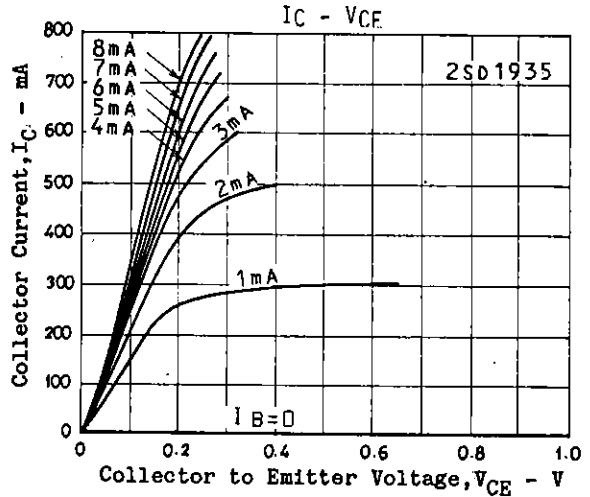
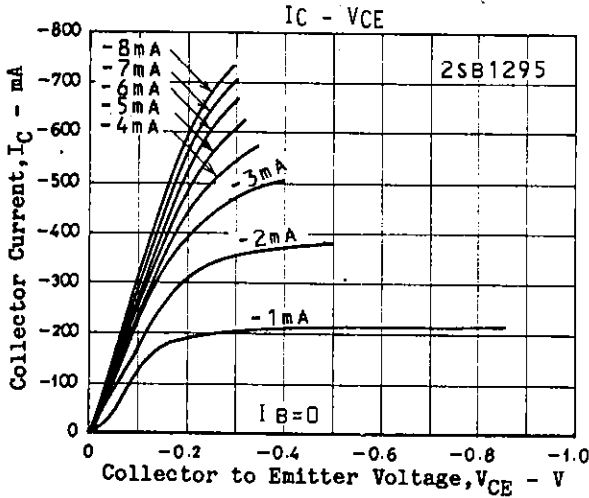
Package Dimensions 2018A

(unit:mm)

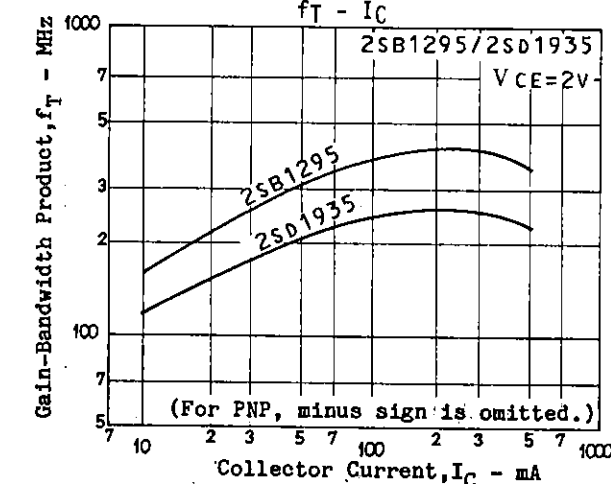
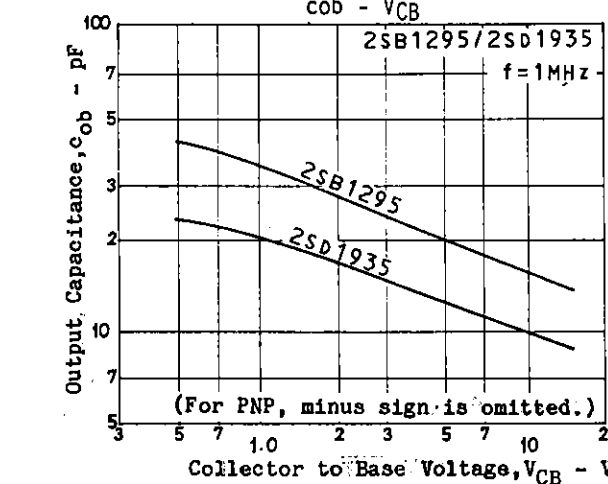
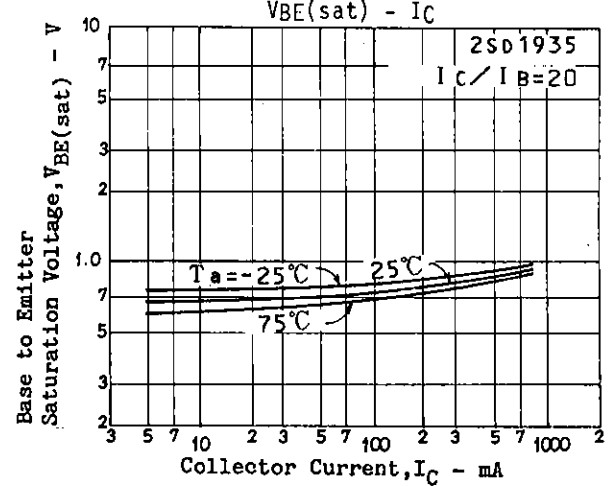
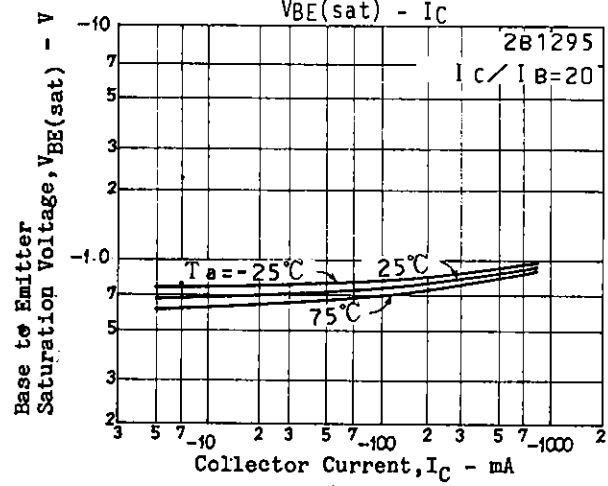
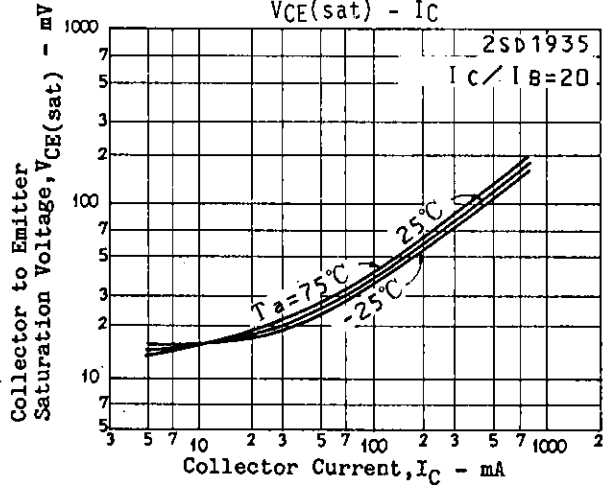
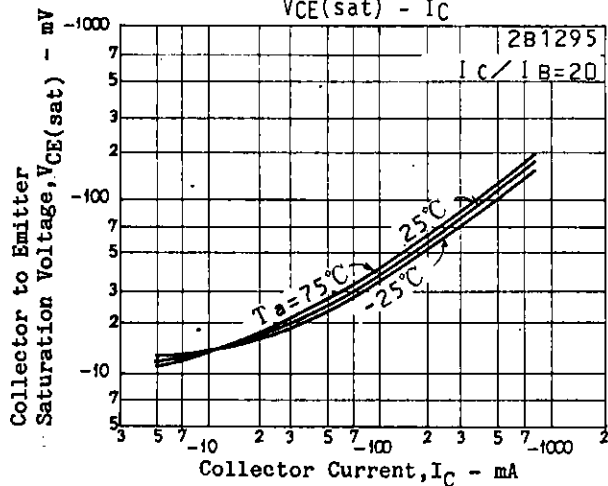
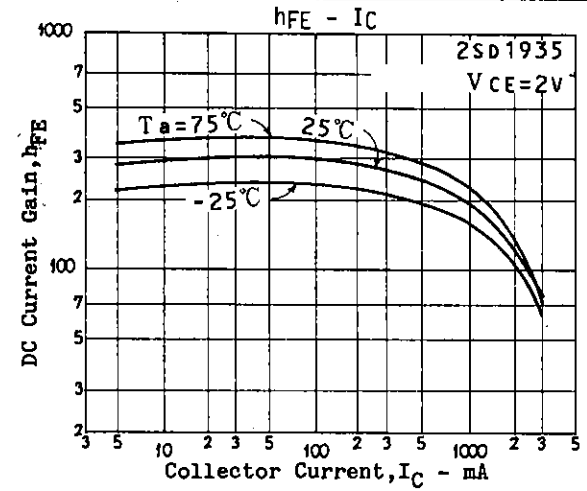
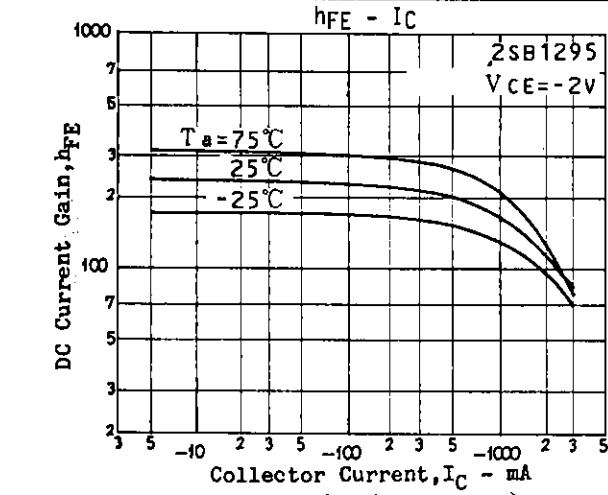


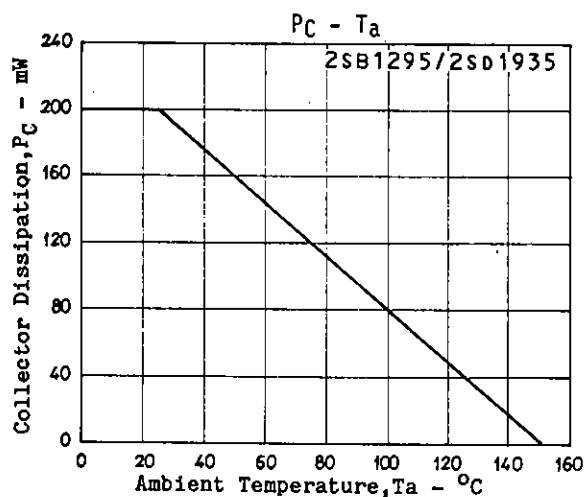
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			min	typ	max	unit
C-E Saturation Voltage	$V_{CE(sat)1}$	$I_C = (-)5mA, I_B = (-)0.5mA$	(-)10	(-)25		mV
	$V_{CE(sat)2}$	$I_C = (-)400mA, I_B = (-)20mA$	(-)100	(-)200		mV
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = (-)400mA, I_B = (-)20mA$	(-)0.9	(-)1.2		V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)10\mu A, I_E = 0$	(-)15			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)1mA, R_{BE} = \infty$	(-)15			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)10\mu A, I_C = 0$	(-)5			V



2SB1295/2SD1935





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